



P-CHANNEL ENHANCEMENT MODE MOSFET

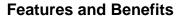
Product Summary

V _{(BR)DSS}	R _{DS(on)} max	Ι _D T _A = 25°C
001/	$70m\Omega@V_{GS} = -10V$	-3.8A
-30V	120m Ω @ V _{GS} =-4.5V	-3.0A

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power management functions
- Analog Switch
- Load Switch
- Boost Switch



- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

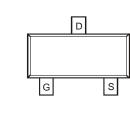
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020

Gate

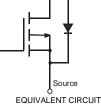
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Top View



Pin Configuration



Drair

Ordering Information (Note 3)

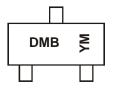
Case	Packaging
SOT23	3000/Tape & Reel
	SOT23

1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



DMB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characterist	ic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage		V _{GSS}	±20	V	
Drain Current (Note 4) V _{GS} = -10V	Steady State	$T_A = 25^{\circ}C$ $T_A = 70^{\circ}C$	ID	-3.8 -2.9	А
Pulsed Drain Current (Note 5)			I _{DM}	-11	А

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	PD	1.08	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 4)	$R_{ heta JA}$	115	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

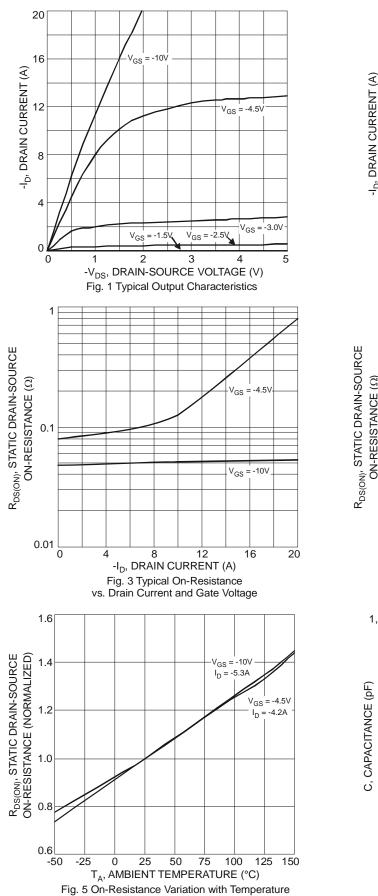
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						•
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_		-800	nA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-1.0	-1.8	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance	P		56	70	mΩ	$V_{GS} = -10V, I_D = -3.8A$
	R _{DS (ON)}	_	98	120	1115.2	$V_{GS} = -4.5V, I_D = -3.0A$
Forward Transfer Admittance	Y _{fs}	_	3.6	_	S	$V_{DS} = -5V, I_D = -2.7A$
Diode Forward Voltage (Note 6)	V _{SD}	_	_	-1.26	V	$V_{GS} = 0V, I_{S} = -2.7A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss	_	336	1008	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	_	70	210	pF	
Reverse Transfer Capacitance	Crss	_	49	147	pF	
Gate Resistance	R _G	_	4.6	_	Ω	$V_{GS} = 0V V_{DS} = 0V, f = 1MHz$
SWITCHING CHARACTERISTICS (Note 7)						
Total Gate Charge	Qq	—	4.0	8.0		V _{DS} = -15V, V _{GS} = -4.5V, I _D = -3.8A
	Ū.	_	7.8	_	nC	
Gate-Source Charge	Q _{gs}	_	1.0	_		$V_{DS} = -15V, V_{GS} = -10V,$ $I_D = -3.8A$
Gate-Drain Charge	Q _{gd}	_	2.5	_		
Turn-On Delay Time	t _{d(on)}	_	6.0	12.0		
Rise Time	tr	_	5.0	10.0		$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{d(off)}	_	17.6	35.2	ns	$I_{\rm D} = -1A, R_{\rm G} = 6.0\Omega$
Fall Time	t _f		9.5	19.0	1	

4. Device mounted on FR-4 PCB on 2 oz., 0.5 in.² copper pads and t \leq 5 sec. 5. Pulse width \leq 10µS, Duty Cycle \leq 1%. Notes:

6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.





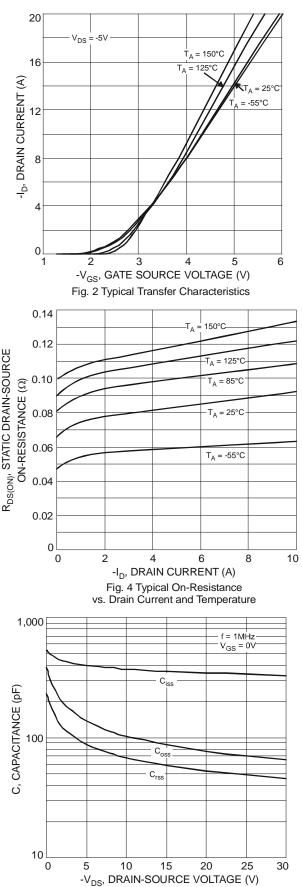
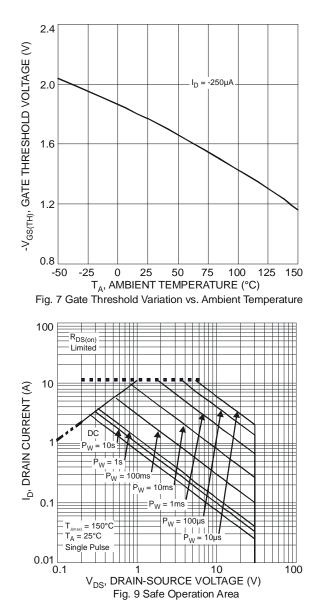
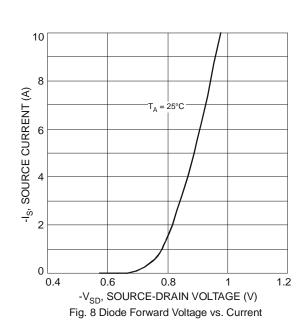


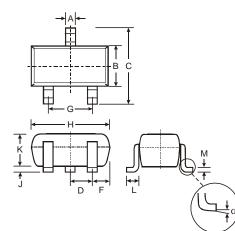
Fig. 6 Typical Capacitance







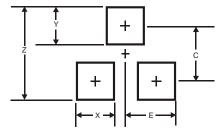
Package Outline Dimensions



SOT23						
Dim	Min	Max				
Α	0.37	0.51				
В	1.20	1.40				
С	2.30	2.50				
D	0.89	1.03				
F	0.45	0.60				
G	1.78	2.05				
Н	2.80	3.00				
J	0.013	0.10				
K	0.903	1.10				
L	0.45	0.61				
М	0.085	0.180				
α	0°	8°				



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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